

Please replace the claims with the following clean version of the entire set of pending claims, in accordance with 37 C.F.R. § 1.121(c)(1)(i). Cancel all previous versions of any pending claim.

A marked up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 C.F.R. § 1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

CLAIMS

✓
Please cancel claims 1-20.

21. A conductive line comprising:
a polysilicon layer; and
a metal-silicide layer against the layer of polysilicon, the metal-silicide layer comprising a Group III dopant or a Group V dopant.
22. The conductive line of claim 21 wherein the metal-silicide layer comprises a concentration of the dopant of at least about 1×10^{18} ions/cm³.
23. A metal-silicide layer comprising a Group III dopant or a Group V dopant.
24. The metal-silicide of claim 23 comprising a concentration of the dopant of at least about 1×10^{18} ions/cm³.

25. A programmable-read-only-memory device comprising:
- a first dielectric layer over a substrate;
 - a floating gate over the first dielectric layer;
 - a second dielectric layer over the floating gate;
 - a conductive line over the second dielectric layer; and
 - a metal-silicide layer over the conductive line, the metal-silicide layer comprising a Group III dopant or a Group V dopant.
26. The programmable-read-only-memory device of claim 25 wherein the device is an EPROM.
27. The programmable-read-only-memory device of claim 25 wherein the device is an EEPROM.
28. The programmable-read-only-memory device of claim 25 wherein the metal-silicide layer comprises a concentration of the dopant of at least about 1×10^{18} ions/cm³.